

NPN SILICON TRANSISTOR

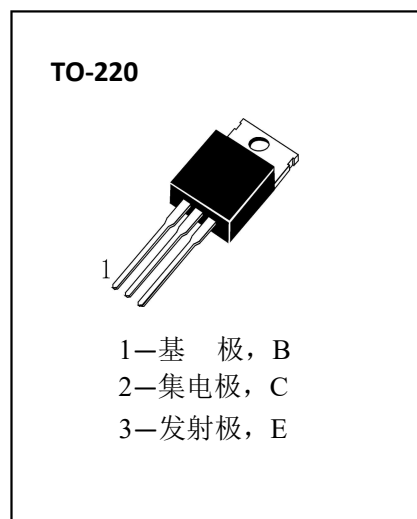
■ 主要用途

音频功率放大。

■ 极限值 (Ta=25℃)

Tstg——贮存温度.....	-55~150℃
Tj——结温.....	150℃
PC——集电极功率耗散 (TC=25℃)	65W
PC——集电极功率耗散 (TA=25℃)	2W
VCBO——集电极—基极电压.....	100V
VCEO——集电极—发射极电压.....	100V
VEBO——发射极—基极电压.....	5V
IC——集电极电流.....	6A
IB——基极电流.....	2A

■ 外形图及引脚排列



■ 电参数 (Ta=25℃)

参数符号	符 号 说 明	最小值	典型值	最大值	单 位	测 试 条 件
ICEO	集电极—发射极截止电流			0.7	mA	VC=60V, IB=0
IEBO	集电极—基极截止电流			1	mA	VE=5V, IC=0
ICES	集电极—发射极饱和电流			400	μA	VC=100V, VE=0
HFE(1)	直流电流增益	30				VC=4V, IC=0.3A
HFE(2)		15		80		VC=4V, IC=3A
VCE(sat)	集电极—发射极饱和压降			1.5	V	IC=6A, IB=600mA
VBE(on)	基极—发射极导通电压			2.0	V	VC=4V, IC=6A
BVCEO	集电极—发射极击穿电压	100			V	IC=30mA, IB=0
fT	特征频率	3.0			MHz	VC=10V, IC=500mA f=1MHz

■ 典型特性曲线

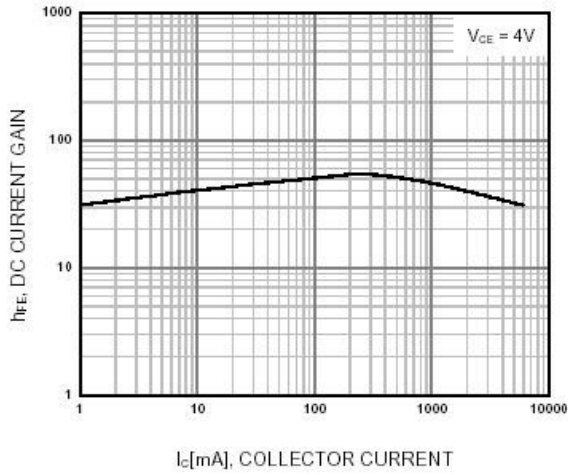


Figure 1. DC current Gain

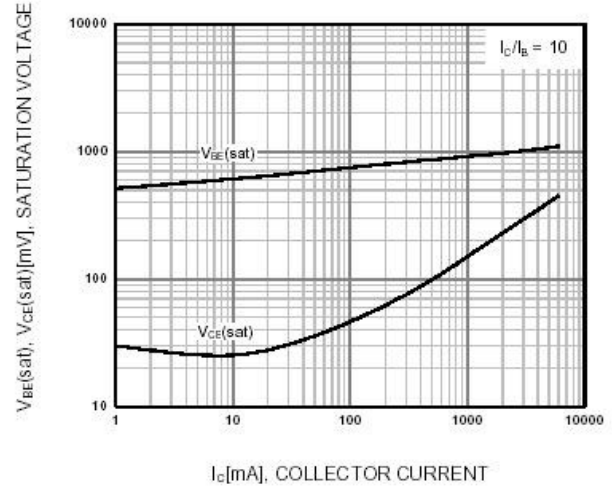


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

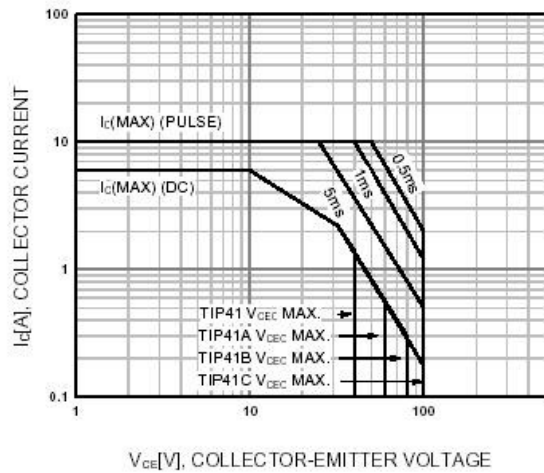


Figure 3. Safe Operating Area

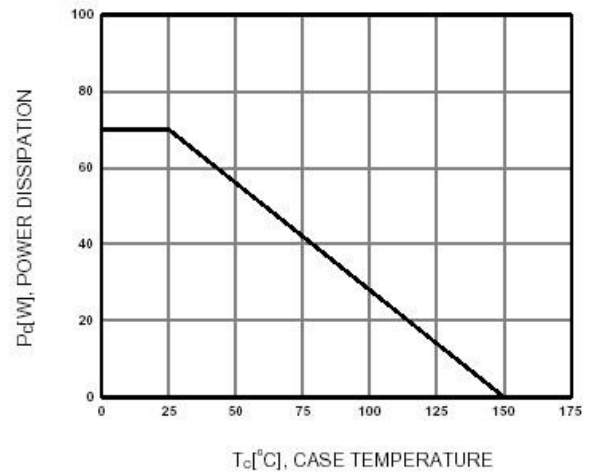


Figure 4. Power Derating



NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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